NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE9435A uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_{D} = -5.3A$

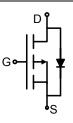
 $R_{DS(ON)}$ < 85m Ω @ V_{GS} =-4.5V

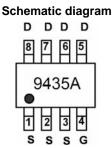
 $R_{DS(ON)}$ < 49m Ω @ V_{GS} =-10V

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management





Marking and pin Assignment



SOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
9435A	NCE9435A	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	-5.3	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-20	Α
Maximum Power Dissipation	P _D	2.6	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	49	°C/W
	00/1		1

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μΑ



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Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1	-1.6	-3	٧	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-5.3A	-	37	49	mΩ	
Dialii-Source Oii-State Resistance		V _{GS} =-4.5V, I _D =-4.2A	-	60	85	mΩ	
Forward Transconductance	g FS	V _{DS} =-15V,I _D =-4.5A	4	7	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	\/ - 15\/\/ -0\/	-	1040	-	PF	
Output Capacitance	Coss	- V _{DS} =-15V,V _{GS} =0V, - F=1.0MHz	-	420	-	PF	
Reverse Transfer Capacitance	C _{rss}	- F - 1.0WII 12	-	150	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	15	ı	nS	
Turn-on Rise Time	t _r	V _{DD} =-15V, ID=-1A,	-	13	ı	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{GEN} =6 Ω	-	58	ı	nS	
Turn-Off Fall Time	t _f		-	21	ı	nS	
Total Gate Charge	Qg		-	12	ı	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =-15V,I _D =-5.3A,V _{GS} =-10V	-	2.2	-	nC	
Gate-Drain Charge	Q_{gd}			3	1	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.7A	-	-	-1.2	V	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

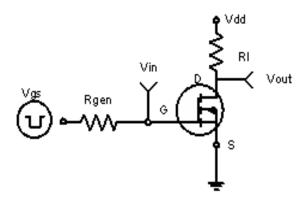


Figure 1:Switching Test Circuit

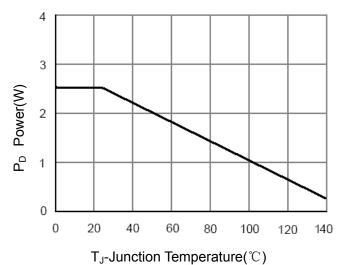


Figure 3 Power Dissipation

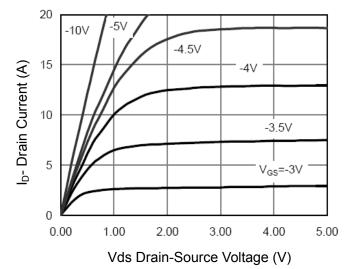


Figure 5 Output Characteristics

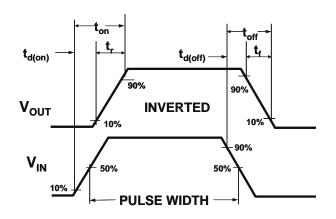


Figure 2:Switching Waveforms

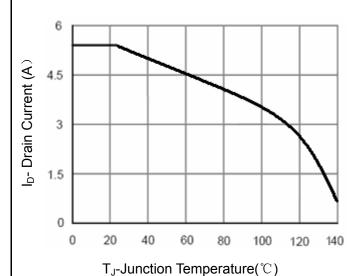


Figure 4 Drain Current

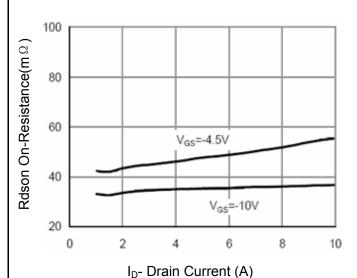
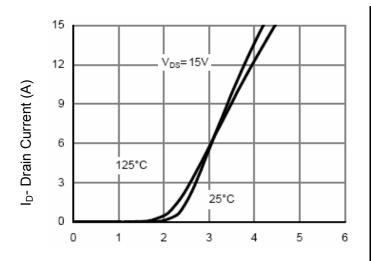
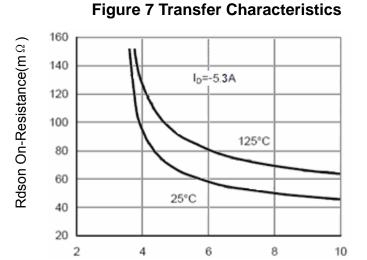


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)



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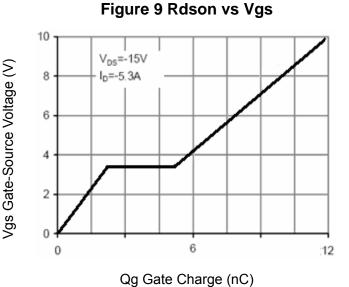
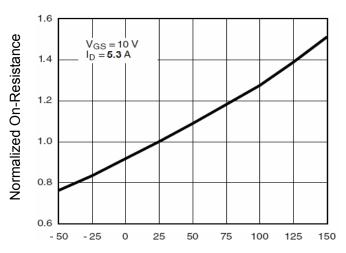
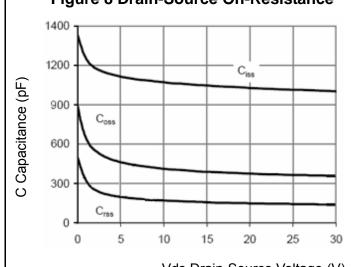


Figure 11 Gate Charge



T_J-Junction Temperature(℃)

Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

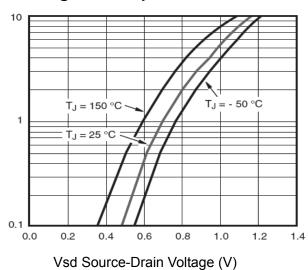


Figure 12 Source- Drain Diode Forward

Is- Reverse Drain Current (A)



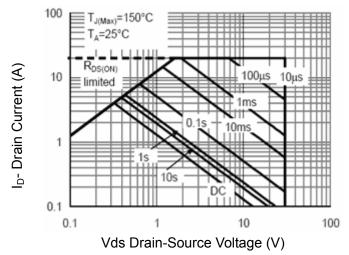


Figure 13 Safe Operation Area

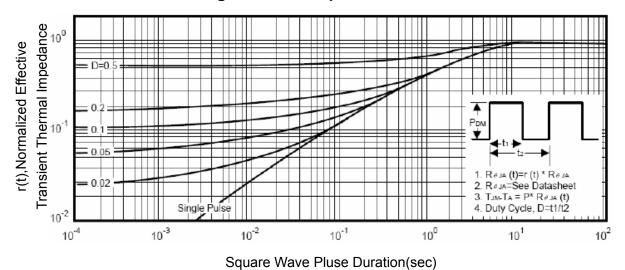
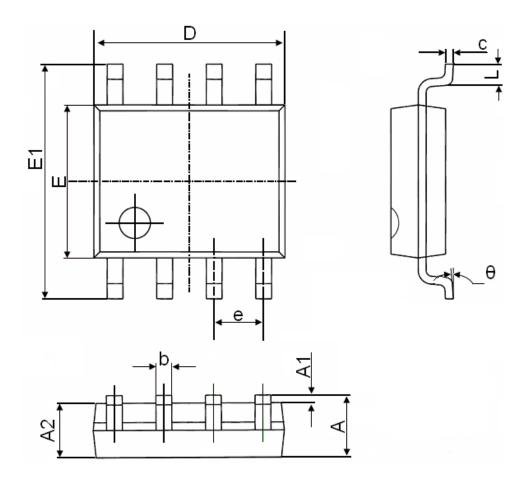


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

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